

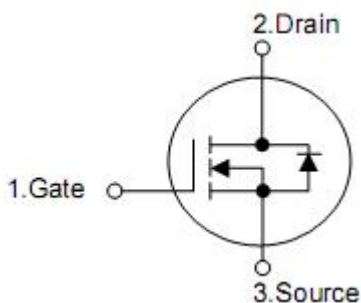
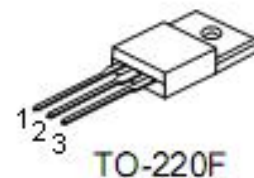
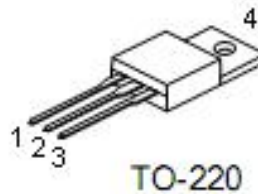
1. Product Features

- RoHS Compliant
- $R_{DS(ON),typ.}=9.6\Omega@V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

2. Applications

- Adaptor
- Charger
- SMPS Standby Power

3. Pin configuration



Pin	Function
1	Gate
2	Drain
3	Source
4	Drain

4. Ordering Information

Part Number	Package	Brand
KND41100A	TO-252	KIA
KNP41100A	TO-220	KIA
KNF41100A	TO-220F	KIA

5. Absolute maximum ratings

(T_c= 25 °C , unless otherwise specified)

Symbol	Parameter	Ratings	Unit
V _{DSS}	Drain-to-Source Voltage T _J =25 °C	1000	V
V _{GSS}	Gate-to-Source Voltage	±30	
I _D	Continuous Drain Current @ T _c =25 °C	2.0	A
I _{DM}	Pulsed Drain Current at V _{GS} =10V Limited by T _{Jmax}	8.0	
E _{AS}	Single Pulse Avalanche Energy(V _{DD} =50V)	80	mJ
P _D	Maximum Power Dissipation	60	W
T _{Jmax}	Max. Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	

6. Thermal characteristics

Symbol	Parameter	Ratings	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	2.08	°C /W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	75	

7. Electrical characteristics

(T_J=25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-to-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	1000	--	--	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} =1000V, V _{GS} =0V	--	--	1	uA
I _{GSS}	Gate-to-Source Leakage Current	V _{GS} =±30V, V _{DS} =0V	-100	--	100	nA
R _{DS(ON)}	Drain-to-Source ON Resistance	V _{GS} =10V, I _D =1.0A		9.6	12	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2.0	--	4.0	V
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1.0MHZ	--	370	--	pF
C _{rss}	Reverse Transfer Capacitance		--	4.0	--	
C _{oss}	Output Capacitance		--	40	--	
Q _g	Total Gate Charge	V _{DD} =500V, I _D =2.0A, V _{GS} =10V	--	15	--	nC
Q _{gs}	Gate-to-Source Charge		--	2.1	--	
Q _{gd}	Gate-to-Drain (Miller) Charge		--	6.0	--	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =500V, I _D =2.0A, R _G =12Ω V _{GS} = 10V (Resistive Load)	--	8.0	--	nS
t _{rise}	Rise Time		--	6.0	--	
t _{d(OFF)}	Turn-Off Delay Time		--	36	--	
t _{fall}	Fall Time		--	15	--	
I _{SD}	Continuous Source Current		--	--	2	A
V _{SD}	Forward Voltage	I _S =2.0A, V _{GS} =0V	--	-	1.5	V
t _{rr}	Reverse recovery time	V _{GS} =0V, I _F =2.0A, diF/dt=-100A/μs	--	320	--	ns
Q _{rr}	Reverse recovery charge		--	1.0	--	uC

8. Test circuits and waveforms

Fig. 1. Output Characteristics @ 25°C

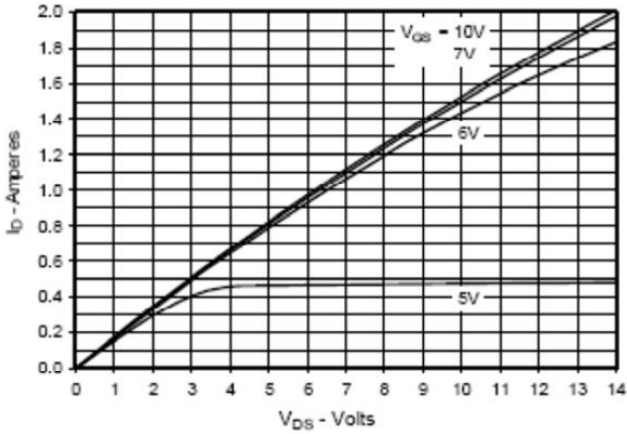


Fig. 2. Extended Output Characteristics @ 25°C

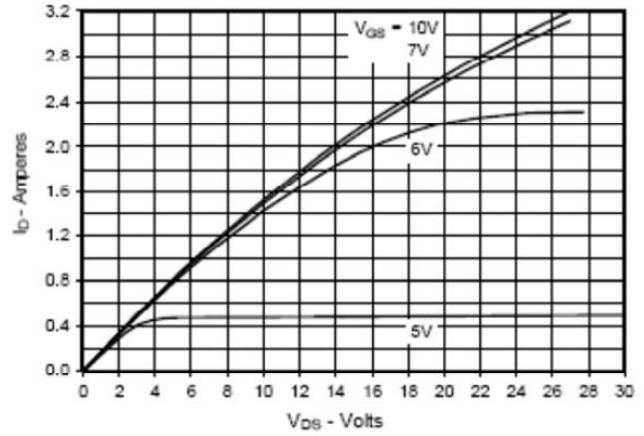


Fig. 3. Output Characteristics @ 125°C

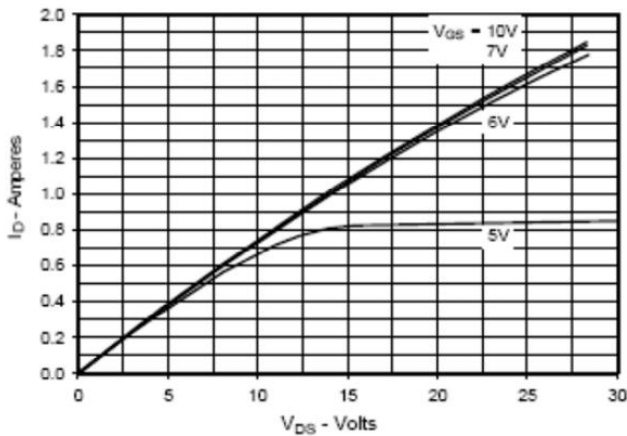


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 1A$ Value vs. Junction Temperature

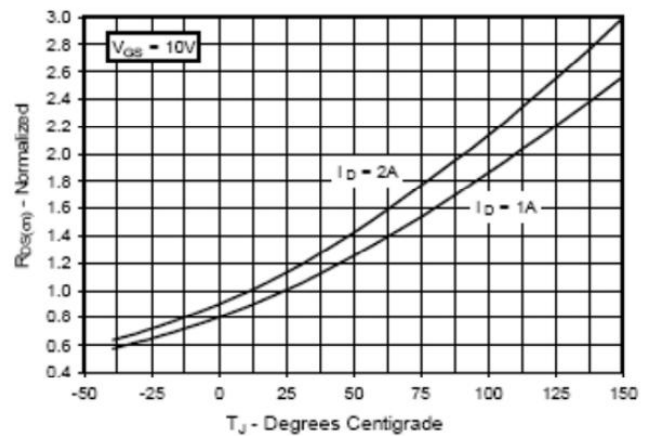


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 1A$ Value vs. Drain Current

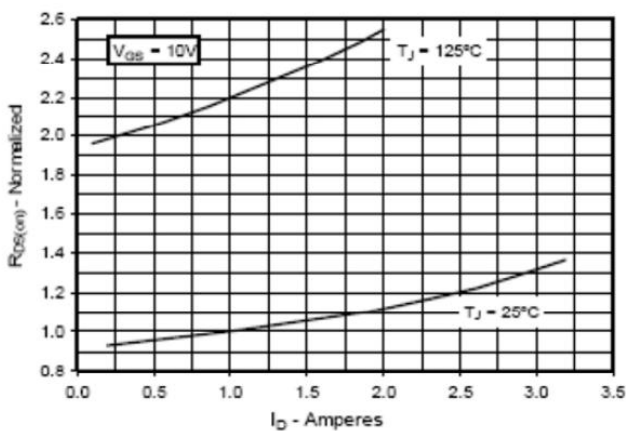


Fig. 6. Maximum Drain Current vs. Case Temperature

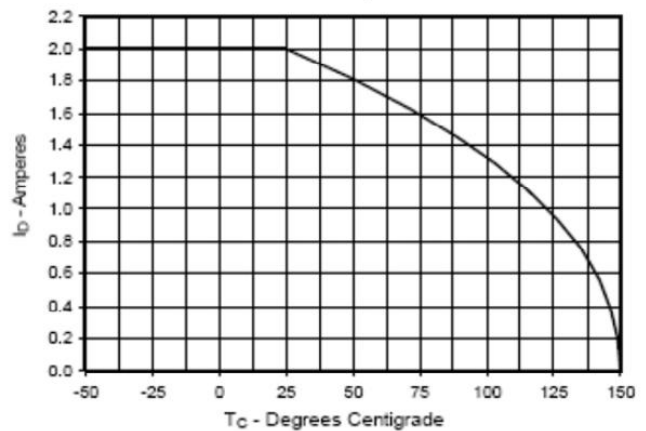


Fig. 7. Input Admittance

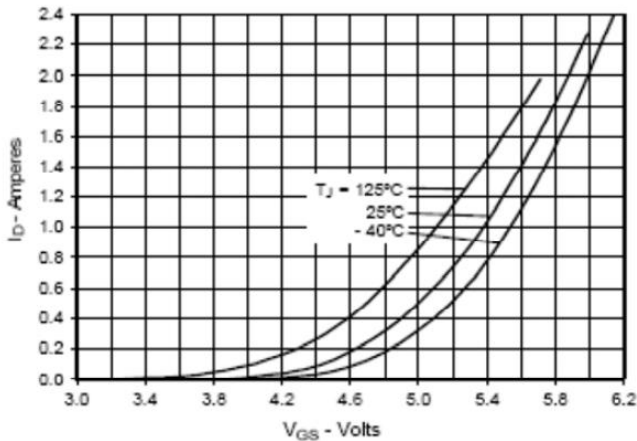


Fig. 8. Transconductance

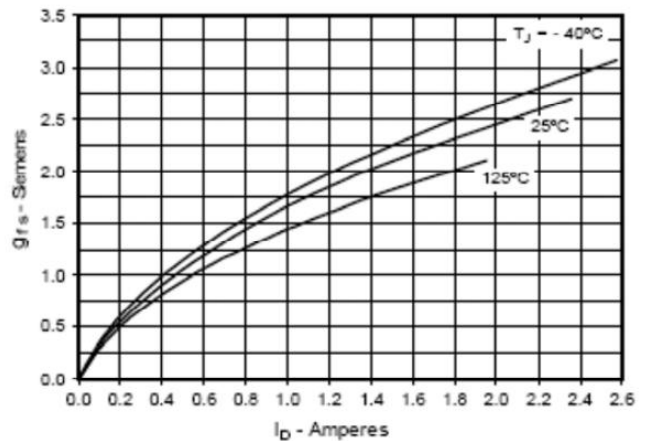


Fig. 9. Forward Voltage Drop of Intrinsic Diode

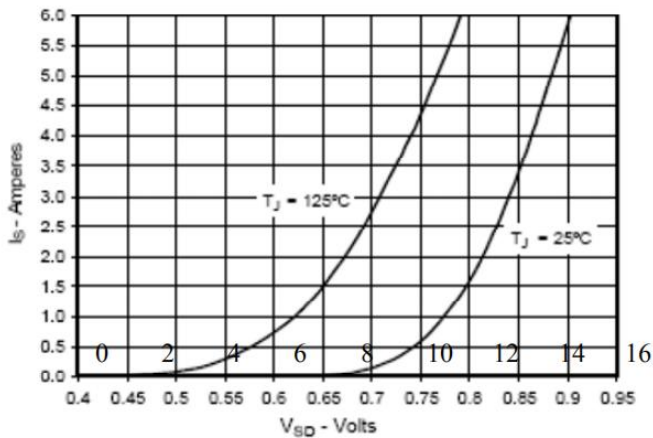


Fig. 10. Gate Charge

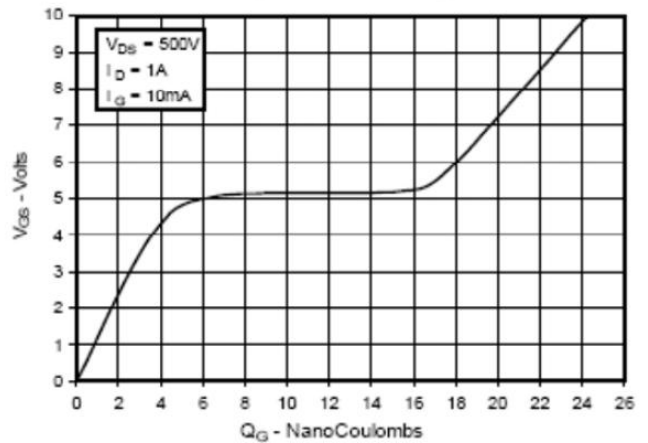


Fig. 11. Capacitance

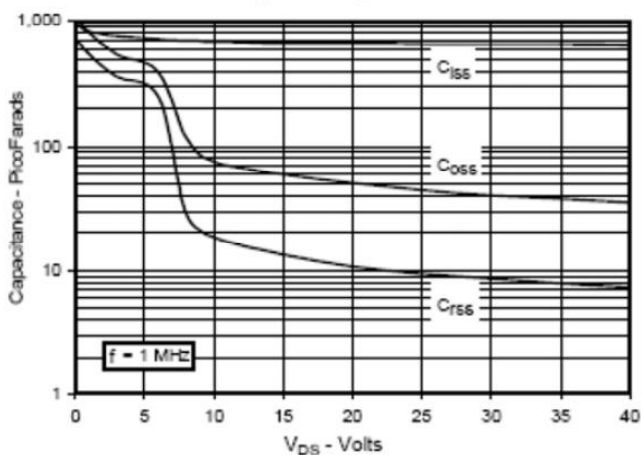


Fig. 12. Maximum Transient Thermal Impedance

